



# 74V1G03

## SINGLE 2-INPUT OPEN DRAIN NAND GATE

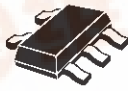

- HIGH SPEED:  $t_{PD} = 3.7 \text{ ns}$  (TYP.) at  $V_{CC} = 5V$
- LOW POWER DISSIPATION:  
 $I_{CC} = 1 \mu\text{A}$  (MAX.) at  $T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (MIN.)
- POWER DOWN PROTECTION ON INPUTS
- OPERATING VOLTAGE RANGE:  
 $V_{CC} \text{ (OPR)} = 2V \text{ to } 5.5V$
- IMPROVED LATCH-UP IMMUNITY

### DESCRIPTION

The 74V1G03 is an advanced high-speed CMOS SINGLE 2-INPUT OPEN DRAIN NAND GATE fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

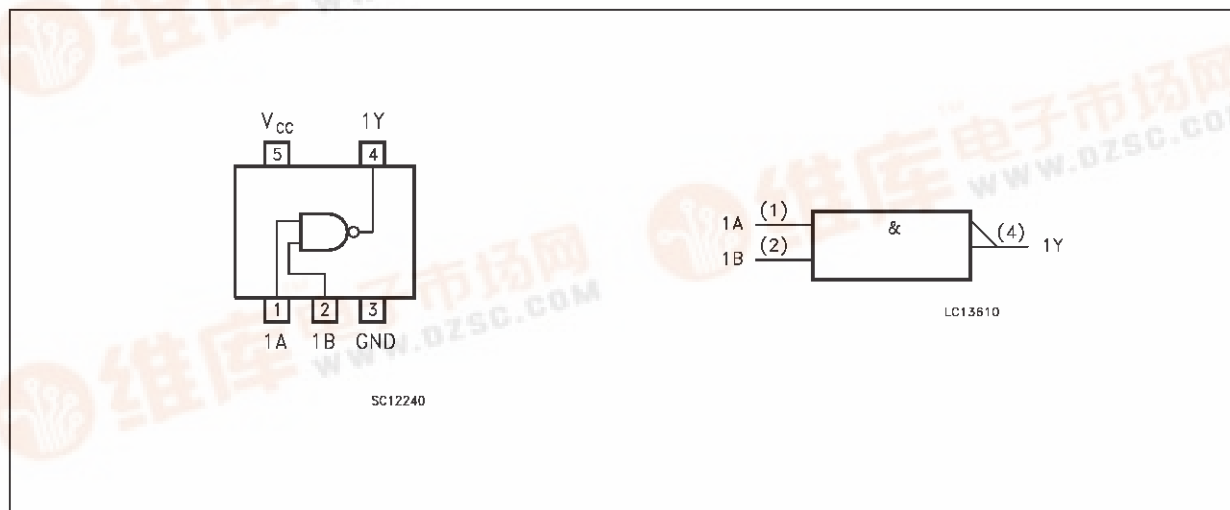
### PRELIMINARY DATA

	
<b>S</b> (SOT23-5L)	<b>C</b> (SC-70)
<b>ORDER CODE:</b>	
74V1G03S	74V1G03C

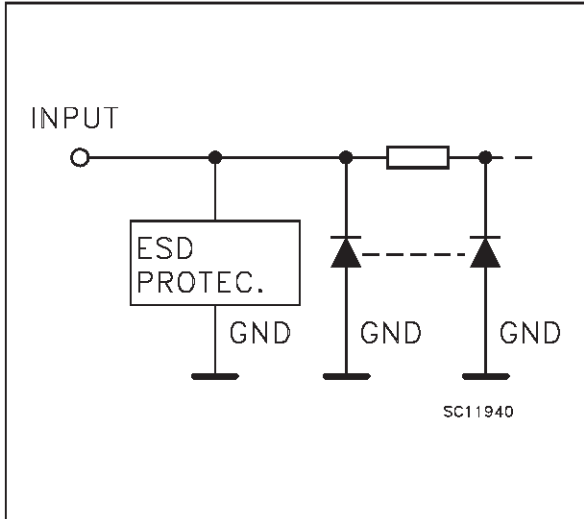
This device can, with an external pull-up resistor, be used in wired AND configuration. This device can also be used as a led driver in any other application requiring a current sink.

Power down protection is provided on all inputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



**INPUT EQUIVALENT CIRCUIT**



**PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1	1A	Data Input
2	1B	Data Input
4	1Y	Data Output
3	GND	Ground (0V)
5	V <sub>CC</sub>	Positive Supply Voltage

**TRUTH TABLE**

A	B	Y
L	L	Z
L	H	Z
H	L	Z
H	H	L

Z: High Impedance

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	2.0 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to 5.5	V
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-40 to +85	°C
dt/dv	Input Rise and Fall Time (see note 1) (V <sub>CC</sub> = 3.3 ± 0.3V) (V <sub>CC</sub> = 5.0 ± 0.5V)	0 to 100 0 to 20	ns/V ns/V

1) V<sub>IN</sub> from 30% to 70% of V<sub>CC</sub>

## DC SPECIFICATIONS

Symbol	Parameter	Test Conditions			Value					Unit
		V <sub>CC</sub> (V)			T <sub>A</sub> = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
V <sub>IH</sub>	High Level Input Voltage	2.0			1.5			1.5		V
		3.0 to 5.5			0.7V <sub>CC</sub>			0.7V <sub>CC</sub>		
V <sub>IL</sub>	Low Level Input Voltage	2.0					0.5		0.5	V
		3.0 to 5.5					0.3V <sub>CC</sub>		0.3V <sub>CC</sub>	
V <sub>OL</sub>	Low Level Output Voltage	2.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		V
		3.0	I <sub>O</sub> =50 μA		0.0	0.1		0.1		
		4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1		
		3.0	I <sub>O</sub> =4 mA			0.36		0.44		
		4.5	I <sub>O</sub> =8 mA			0.36		0.44		
I <sub>OZ</sub>	High Impedance Output Leakage Current	5.5	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = V <sub>CC</sub> or GND			±0.25		±2.5	μA	
I <sub>I</sub>	Input Leakage Current	0 to 5.5	V <sub>I</sub> = 5.5V or GND			±0.1		±1.0	μA	
I <sub>CC</sub>	Quiescent Supply Current	5.5	V <sub>I</sub> = V <sub>CC</sub> or GND			2		20	μA	

AC ELECTRICAL CHARACTERISTICS (Input t<sub>r</sub> = t<sub>f</sub> = 3 ns)

Symbol	Parameter	Test Condition			Value					Unit
		V <sub>CC</sub> (V)	C <sub>L</sub> (pF)		T <sub>A</sub> = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
t <sub>PZL</sub>	Propagation Delay Time	3.3 <sup>(*)</sup>	15	R <sub>L</sub> = 1 KΩ		5.5	7.9	1.0	9.5	ns
		3.3 <sup>(*)</sup>	50	R <sub>L</sub> = 1 KΩ		8.0	11.4	1.0	13.0	
		5.0 <sup>(**)</sup>	15	R <sub>L</sub> = 1 KΩ		3.7	5.5	1.0	6.5	
		5.0 <sup>(**)</sup>	50	R <sub>L</sub> = 1 KΩ		5.2	7.5	1.0	8.5	
t <sub>PLZ</sub>	Propagation Delay Time	3.3 <sup>(*)</sup>	50	R <sub>L</sub> = 1 KΩ		9.0	11.4	1.0	13.0	ns
		5.0 <sup>(**)</sup>	50	R <sub>L</sub> = 1 KΩ		6.0	7.5	1.0	8.5	

(\*) Voltage range is 3.3V ± 0.3V

(\*\*) Voltage range is 5V ± 0.5V

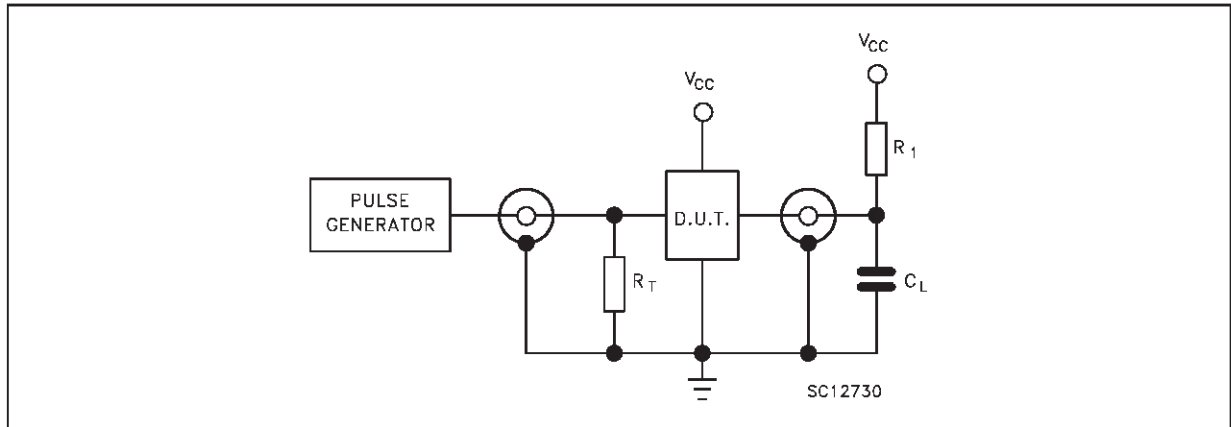
## CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Conditions			Value					Unit
					T <sub>A</sub> = 25 °C			-40 to 85 °C		
					Min.	Typ.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance					4	10		10	pF
C <sub>OUT</sub>	Output Capacitance					5				pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)					6				pF

1) C<sub>PD</sub> is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I<sub>CC(opr)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>IN</sub> + I<sub>CC</sub>

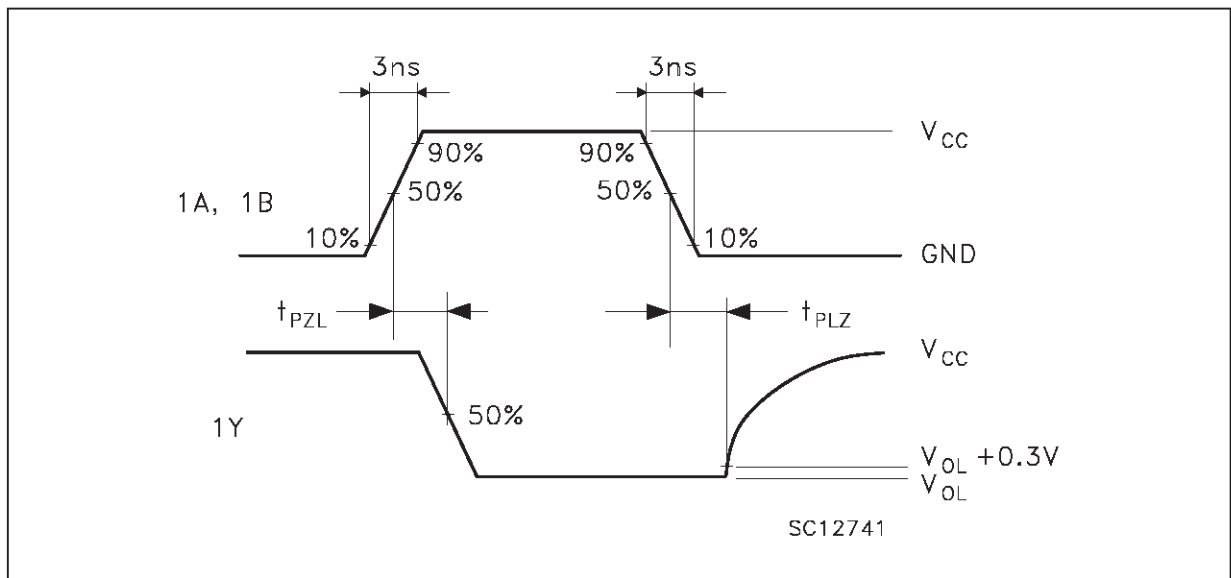
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## TEST CIRCUIT



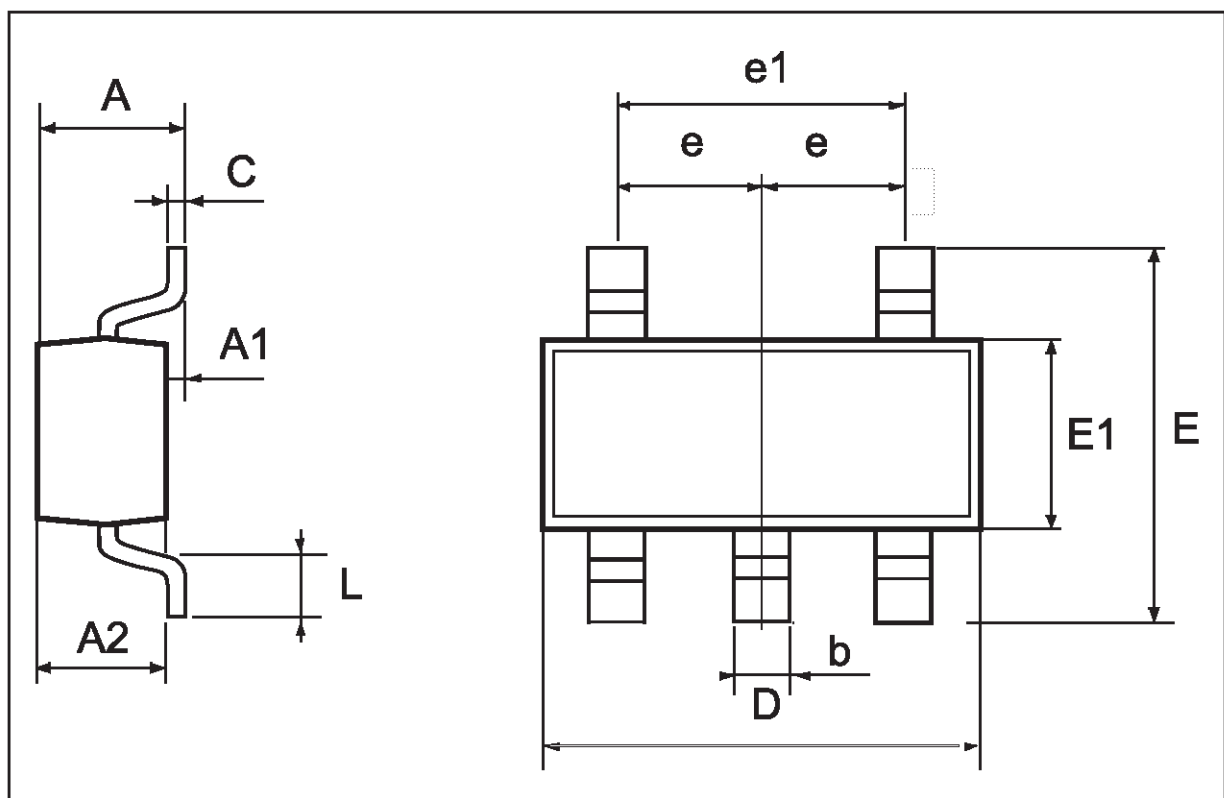
$C_L = 15/50$  pF or equivalent (includes jig and probe capacitance)  
 $R_L = R_1 = 1K\Omega$  or equivalent  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

## WAVEFORM: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)



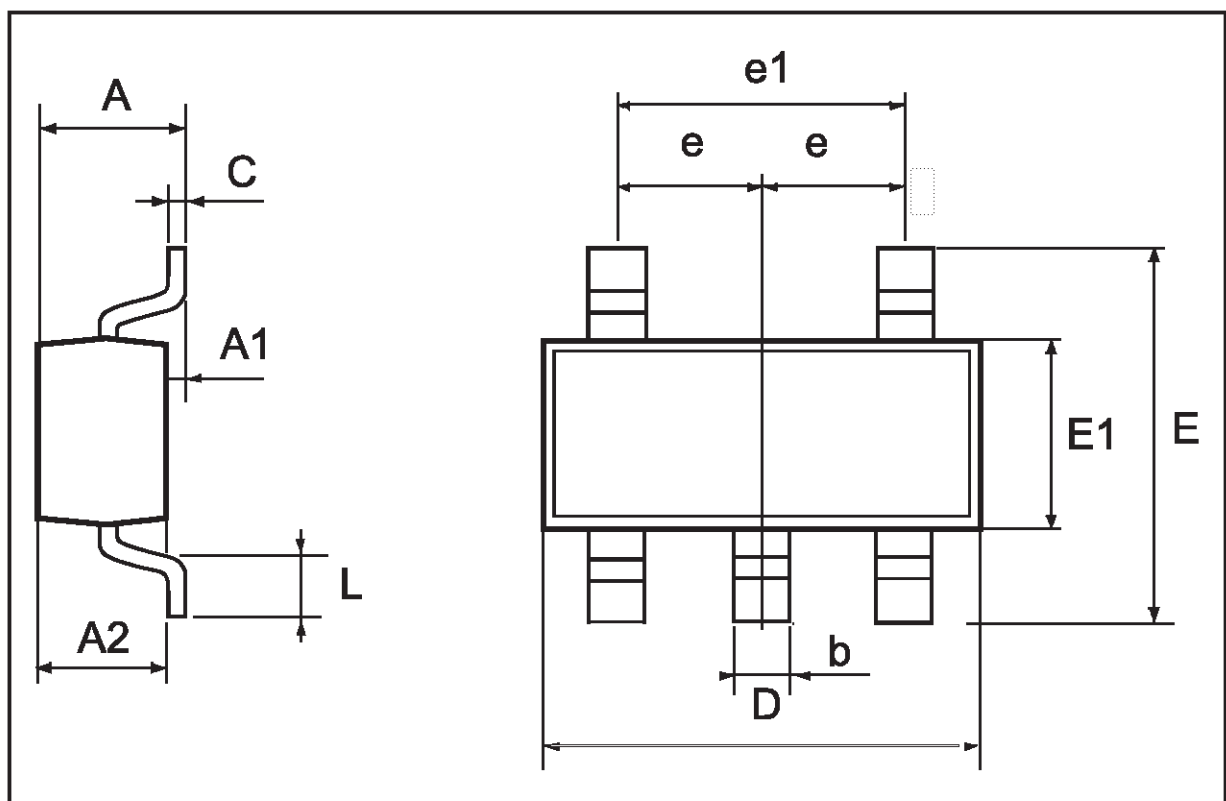
## SOT23-5L MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.35		0.50	13.7		19.7
C	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3		118.1
E1	1.50		1.75	59.0		68.8
L	0.35		0.55	13.7		21.6
e		0.95			37.4	
e1		1.9			74.8	



**SC-70 MECHANICAL DATA**

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.80		1.10	31.5		43.3
A1	0.00		0.10	0.0		3.9
A2	0.80		1.00	31.5		39.4
b	0.15		0.30	5.9		11.8
C	0.10		0.18	3.9		7.1
D	1.80		2.20	70.9		86.6
E	1.80		2.40	70.9		94.5
E1	1.15		1.35	45.3		53.1
L	0.10		0.30	3.9		11.8
e		0.65			25.6	
e1		1.3			51.2	



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